

EAST Search History

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|---------|--|---|------------------|---------|------------------|
| L1 | 1312 | (metal adj layer) with silicid\$6 with anneal\$4 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/09 08:17 |
| L2 | 158 | 1 and ((dope\$4 or implant\$5) ion transistor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | WITH | ON | 2006/03/09 09:05 |
| L3 | 24 | 2 and inhibit\$4 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | WITH | ON | 2006/03/09 09:09 |
| L4 | 5 | 2 and (inhibit\$4 adj2 ion) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | WITH | ON | 2006/03/09 08:33 |
| L8 | 1312 | ((metal adj layer) with silicid\$6 with anneal\$4) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/09 08:56 |
| L9 | 16 | L8 and (remov\$4 unsilicid\$4 metal) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | AND | ON | 2006/03/09 08:56 |
| L10 | 3 | 9 and ((dope\$4 or implant\$5) (ion or \$2nitrogen or hydrogen or fluorine) transistor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | WITH | ON | 2006/03/09 09:14 |
| L11 | 1 | 2 and ((dope\$4 or implant\$5) inhibit\$4 (ion or \$2nitrogen or hydrogen or fluorine) transistor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | WITH | ON | 2006/03/09 09:04 |
| L12 | 1631621 | semiconductor | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | WITH | ON | 2006/03/09 09:07 |

EAST Search History

| | | | | | | |
|-----|------|--|---|------|----|------------------|
| L13 | 187 | 12 and (metal inhibit\$4 silicide) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | WITH | ON | 2006/03/09 09:54 |
| L14 | 20 | 13 and ((dope\$4 or implant\$5) (ion or \$2nitrogen or hydrogen or fluorine) transistor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | WITH | ON | 2006/03/09 09:56 |
| L15 | 1637 | 12 and (metal (prevent or inhibit\$4) silicide) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | WITH | ON | 2006/03/09 09:55 |
| L16 | 2270 | 12 and (metal (prevent\$4 or inhibit\$4) silicide) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | WITH | ON | 2006/03/09 09:55 |
| L17 | 259 | 16 and ((dope\$4 or implant\$5) (ion or \$2nitrogen or hydrogen or fluorine) transistor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | WITH | ON | 2006/03/09 09:56 |
| L18 | 163 | 17 and anneal\$4 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | WITH | ON | 2006/03/09 09:56 |

EAST Search History

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|---------|--|---|------------------|---------|------------------|
| L1 | 1312 | (metal adj layer) with silicid\$6 with anneal\$4 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/09 08:17 |
| L2 | 158 | 1 and ((dope\$4 or implant\$5) ion transistor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | WITH | ON | 2006/03/09 09:05 |
| L3 | 24 | 2 and inhibit\$4 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | WITH | ON | 2006/03/09 09:09 |
| L4 | 5 | 2 and (inhibit\$4 adj2 ion) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | WITH | ON | 2006/03/09 08:33 |
| L8 | 1312 | ((metal adj layer) with silicid\$6 with anneal\$4) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/09 08:56 |
| L9 | 16 | L8 and (remov\$4 unsilicid\$4 metal) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | AND | ON | 2006/03/09 08:56 |
| L10 | 3 | 9 and ((dope\$4 or implant\$5) (ion or \$2nitrogen or hydrogen or fluorine) transistor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | WITH | ON | 2006/03/09 09:14 |
| L11 | 1 | 2 and ((dope\$4 or implant\$5) inhibit\$4 (ion or \$2nitrogen or hydrogen or fluorine) transistor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | WITH | ON | 2006/03/09 09:04 |
| L12 | 1631621 | semiconductor | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | WITH | ON | 2006/03/09 09:07 |

EAST Search History

| | | | | | | |
|-----|-----|--|---|------|----|------------------|
| L13 | 187 | 12 and (metal inhibit\$4 silicide) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | WITH | ON | 2006/03/09 09:10 |
| L14 | 20 | 13 and ((dope\$4 or implant\$5) (ion or \$2nitrogen or hydrogen or fluorine) transistor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | WITH | ON | 2006/03/09 09:14 |

EAST Search History

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|--------|--|---|------------------|---------|------------------|
| S1 | 769062 | transistor | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/26 10:51 |
| S2 | 5900 | transistor with (metal adj layer) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/26 10:53 |
| S3 | 68 | transistor with ((metal adj layer) with silicid\$6 with anneal\$4) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/26 10:57 |
| S4 | 1281 | ((metal adj layer) with silicid\$6 with anneal\$4) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/26 10:58 |
| S5 | 15 | S4 and (remov\$4 unsilicid\$4 metal) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | AND | ON | 2006/03/09 08:56 |
| S6 | 11 | S5 and (ion implant\$6) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2006/01/26 11:46 |
| S7 | 12 | S5 and (ion near3 implant\$6) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2006/01/26 11:47 |
| S8 | 7 | S4 and (remov\$4 unsilicid\$4 metal) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | WITH | ON | 2006/01/26 11:47 |
| S9 | 5 | S8 and (ion near3 implant\$6) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2006/01/27 09:39 |

EAST Search History

| | | | | | | |
|-----|------|--|---|------|----|------------------|
| S10 | 5280 | 438/592,682,527,530,597,301.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2006/01/27 09:40 |
| S11 | 490 | S10 and (silicid\$6 near3 anneal\$4) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2006/01/27 09:42 |
| S12 | 411 | S11 and implant\$6 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2006/01/27 09:43 |
| S13 | 31 | S12 and (transistor with (metal adj layer)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2006/01/27 09:46 |
| S14 | 12 | S12 and (transistor with substrate with (metal adj layer)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | ADJ | ON | 2006/01/27 09:46 |
| S15 | 69 | transistor with (metal adj layer) with silicid\$6 with anneal\$4 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/08 15:24 |
| S16 | 1309 | (metal adj layer) with silicid\$6 with anneal\$4 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/03/09 08:17 |
| S17 | 618 | (deposit metal transistor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | WITH | ON | 2006/03/08 15:25 |
| S20 | 4 | S17 and (silicid\$5 with (low adj temperature)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | WITH | ON | 2006/03/08 15:29 |